

**Features :**

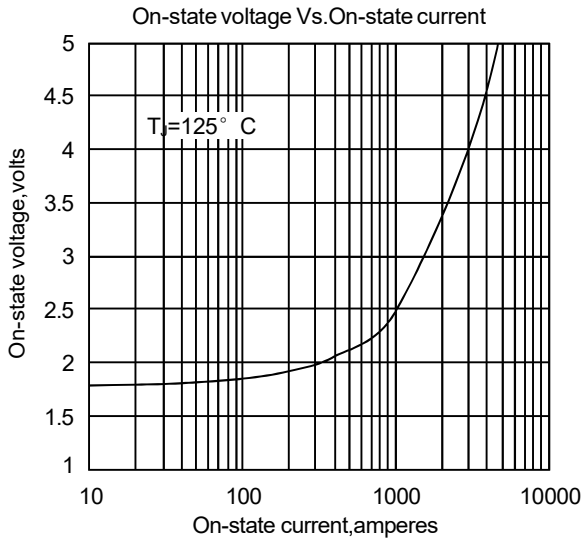
- Isolated mounting base 2500V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

**Typical Applications :**

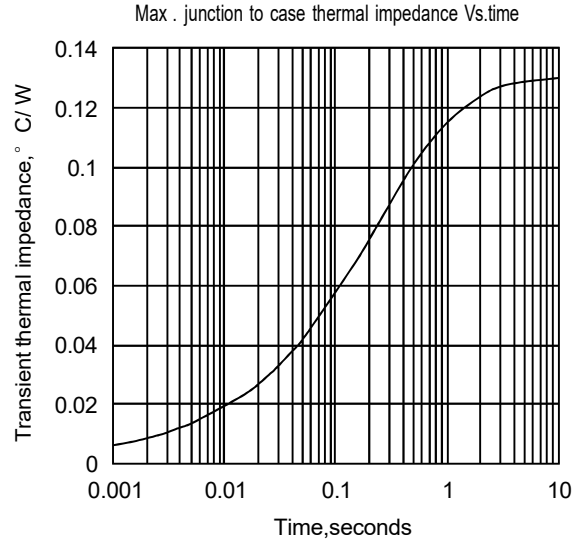
- Inverter
- Inductive heating
- Chopper

V <sub>DSM</sub> , V <sub>RSM</sub>	V <sub>DRM</sub> , V <sub>RRM</sub>	品名
700V	600V	Mx150THF60
900V	800V	Mx150THF80
1100V	1000V	Mx150THF100
1300V	1200V	Mx150THF120
1500V	1400V	Mx150THF140
1700V	1600V	Mx150THF160
1900V	1800V	Mx150THF180

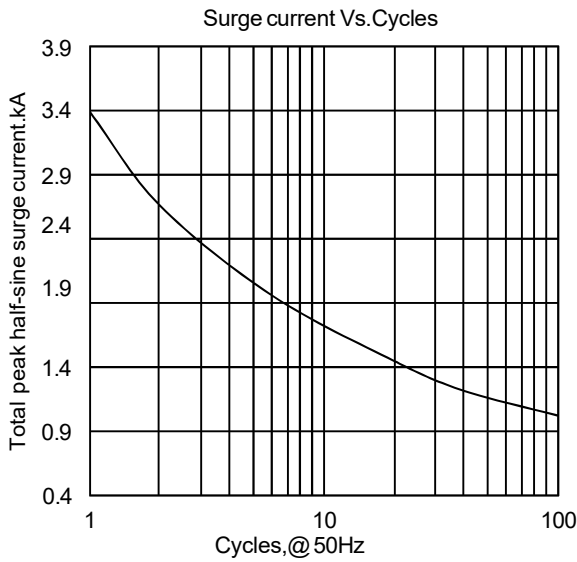
SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T <sub>j</sub> (°C)	VALUE			UNIT	
				Min	Type	Max		
I <sub>T(AV)</sub>	Mean on-state current	180° half sine wave 50Hz Single side cooled, T <sub>c</sub> =85°C	125			150	A	
I <sub>T(RMS)</sub>	RMS on-state current					236	A	
I <sub>DRM</sub> I <sub>RRM</sub>	Repetitive peak current	at V <sub>DRM</sub> at V <sub>RRM</sub>	125			50	mA	
I <sub>TSM</sub>	Surge on-state current	10ms half sine wave V <sub>R</sub> =60%V <sub>RRM</sub>	125			3.4	kA	
I <sup>2</sup> t	I <sup>2</sup> t for fusing coordination					58	10 <sup>3</sup> A <sup>2</sup> s	
V <sub>TO</sub>	Threshold voltage		125			1.78	V	
r <sub>T</sub>	On-state slope resistance					0.70	mΩ	
V <sub>TM</sub>	Peak on-state voltage	I <sub>TM</sub> =450A	25			2.65	V	
dv/dt	Critical rate of rise of off-state voltage	V <sub>DM</sub> =67%V <sub>DRM</sub>	125			800	V/μs	
di/dt	Critical rate of rise of on-state current	Gate source 1.5A t <sub>r</sub> ≤0.5μs Repetitive	125			200	A/μs	
t <sub>q</sub>	Circuit commutated turn-off time	I <sub>TM</sub> =200A, t <sub>p</sub> =4000μs, V <sub>R</sub> =100V dv/dt=30V/μs , di/dt=-20A/μs	125	20		40	μs	
			25	6		16	μs	
I <sub>GT</sub>	Gate trigger current	V <sub>A</sub> =12V, I <sub>A</sub> =1A	25			30	mA	
V <sub>GT</sub>	Gate trigger voltage					0.8	V	
I <sub>H</sub>	Holding current					20	200	mA
I <sub>L</sub>	Latching current						1000	mA
V <sub>GD</sub>	Non-trigger gate voltage	V <sub>DM</sub> = 67%V <sub>DRM</sub>	125			0.2	V	
R <sub>th(j-c)</sub>	Thermal resistance Junction to case	D.C. Single side cooled per chip				0.130	°C/W	
R <sub>th(c-h)</sub>	Thermal resistance case to heatsink	D.C. Single side cooled per chip				0.030	°C/W	
V <sub>iso</sub>	Isolation voltage	50Hz, R.M.S, t=1min, I <sub>iso</sub> :1mA(MAX)		2500			V	
F <sub>m</sub>	Terminal connection torque(M8)			10.0		12.0	N·m	
	Mounting torque(M6)			4.5		6.0	N·m	
T <sub>vj</sub>	Junction temperature			-40		125	°C	
T <sub>slg</sub>	Stored temperature			-40		125	°C	
W <sub>t</sub>	Weight				770		g	
Outline	<b>M03</b>							



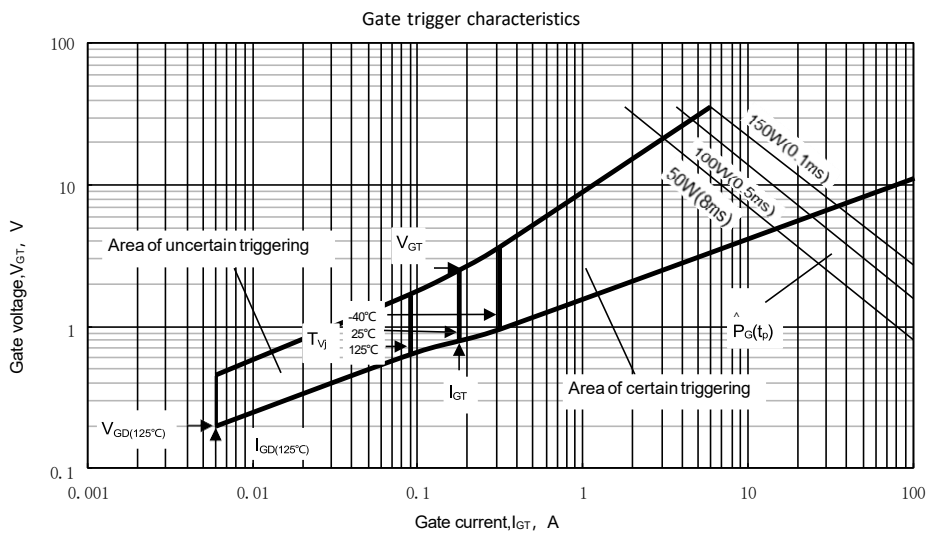
**Fig.1**



**Fig.2**



**Fig.3**



**Fig.4**

